Catalyst-free MBE growth of Mn doped GaAs nanowires on silicon substrates

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Possible methods of formation of as-grown GaMnAs nanowires

- low temperature GaMnAs MBE growth on GaAs(100) with segregated MnAs dots as NW growth catalyst
- high temperature GaAs:Mn MBE growth on Si(100) with Ga droplets inducing the NW growth

CONCLUSIONS:
Mn doped GaAs nanowires were grown by the two methods:
(1) low temperature MBE growth of GaMnAs with MnAs segregation
(2) high temperature MBE growth of GaAs:Mn on Si(100) with Ga nanodroplets

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